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**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

In re Patent Application of

IMAI ET AL.

Serial No. 10/589,390

Filed: August 15, 2006



Atty. Ref.: 1035-650

Group: 2812

Examiner: Unknown

For: Thin Film Transistor, Method of Manufacturing Same, Display Device, Method Of Modifying An Oxide Film, Method of Forming An Oxide Film, Semiconductor Device, Method of Manufacturing Semiconductor Device, and Apparatus For Manufacturing Semiconductor Device

Commissioner for Patents  
P. O. Box 1450  
Alexandria, VA 22313-1450

Sir:

**INFORMATION DISCLOSURE STATEMENT**

As suggested by 37 C.F.R. 1.97, the undersigned attorney brings to the attention of the Patent and Trademark Office the references listed on the attached form PTO-1449.

- All listed documents are attached.
- This application was filed after June 30, 2003 so that copies of U.S. Patent Publications are not required and are not attached.
- Listed foreign patent publications and other documents are enclosed.
- The partial translations were provided to the undersigned by the applicants' foreign representative. The undersigned has no knowledge regarding the pertinency of the partially translated portions vis-à-vis the document as a whole. The partial translations are merely provided for whatever convenience they may be.
- U.S. Publication 2003/0102793 corresponds to the JP 2003-133309 reference cited in the specification; U.S. Publication 2005/0215070 corresponds to the JP 2004-047935 reference cited in the specification; and U.S. Patent 6,221,788 corresponds to the JP 09-045679 reference cited in the specification.

This is not to be construed as a representation that a search has been made or that no better prior art exists, or that a reference is relevant merely because cited.

The Examiner is requested to initial the attached form PTO-1449 and to return a copy of the initialed document to the undersigned as an indication that the attached references have been considered and made of record.

The Commissioner is authorized to charge the undersigned's deposit account #14-1140 in whatever amount is necessary for entry of these papers and the continued pendency of the captioned application.

Respectfully submitted,  
NIXON & VANDERHYE P.C.

April 10, 2007

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## **INFORMATION DISCLOSURE CITATION**

ATTY. DOCKET NO.

1035-650

**APPLICANT**

**SERIAL NO.**

10/589,390

(Use several sheets if necessary)

JMAI ET AL.

FILED DATE

GROUP

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2812

## U.S. PATENT DOCUMENTS

## **FOREIGN PATENT DOCUMENTS**

**OTHER DOCUMENTS (including Author, Title, Date, Pertinent pages, etc.)**

	Sakamoto et al, "Formation of Anodic Reaction Film on n-type Si", Applied Physics, vol. 44, Issue No. 5, 1975, pp.497-506
	Tokuyama, "Comprehensive Treatise on Electronics Technology", Vol. 3, MOS Device, Kogyochosakai, 1976, pp.124-126
	Asuha et al, "Ultrathin Silicon Dioxide Layers with a Low Leakage Current Density Formed by Chemical Oxidation of Si", Applied Physics Letters, Vol. 81, No. 18, 28 October 2002, pp. 3410-3412
	Kobayashi et al, "Nitric Acid Oxidation of Si to Form Ultrathin Silicon Dioxide Layers with a Low Leakage Current Density", Journal of Applied Physics, Vol. 94, No. 11, American Institute of Physics, 2003, pp. 7328-7335
	Asuha et al, "Low Temperature Formation o Sio2/Si Structure by Chemical Method and Spectroscopic Observation", Meeting Abstracts of the Physical Society of Japan, Vol. 58, Issue 2, Part 2, Meeting Abstracts, 2003, pp. 771-

Examiner: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to application.

Form PTO-FB-A820 (Also PTO-1449)